

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	5	("6465311" or "6391720" or "6225173" or "4616400" or "5814544").pn.	US-PGPUB; USPAT	OR	OFF	2005/05/26 16:42
L2	6332	(soi "silicon-on-insulator" sos "silicon-on-sapphire" box (buried adj oxide) (silicon near epitax\$8)) same (sige gesi (silicon near germanium))	US-PGPUB; USPAT	OR	ON	2005/05/26 17:40
L3	53	L2 same ((source drain) with (elevat\$10 rais\$6))	US-PGPUB; USPAT	OR	ON	2005/05/26 16:48
L4	24	L2 same ((gate channel) near2 (recess\$6 trench groove damascene inlaid "in-laid"))	US-PGPUB; USPAT	OR	ON	2005/05/26 16:56
L5	667	(soi "silicon-on-insulator" sos "silicon-on-sapphire" box (buried adj oxide) (silicon near epitax\$8)) same (sige gesi (silicon near germanium))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 16:59
L6	6	L5 and ((gate channel) with (recess\$6 trench groove damascene inlaid "in-laid"))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 16:59
L7	4	L5 and ((source drain) same (elevat\$10 rais\$6))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 17:00
L8	446	L2 and ((source drain) with (elevat\$10 rais\$6))	US-PGPUB; USPAT	OR	ON	2005/05/26 17:01
L9	5621	438/151.ccls. 438/270.ccls. 438/295.ccls. 438/300.ccls. 438/589.ccls. 438/595.ccls. 257/347.ccls. 257/387.ccls.	US-PGPUB; USPAT	OR	ON	2005/05/26 17:01
L10	92	L8 and L9	US-PGPUB; USPAT	OR	ON	2005/05/26 17:01
L11	987	L9 and ((gate channel) near2 (recess\$6 trench groove damascene inlaid "in-laid"))	US-PGPUB; USPAT	OR	ON	2005/05/26 17:13
L12	82	L2 and L11	US-PGPUB; USPAT	OR	ON	2005/05/26 17:13
L13	82	L2 and L11	US-PGPUB; USPAT	OR	ON	2005/05/26 17:25
L14	3435	(soi "silicon-on-insulator" "silicon-on-sapphire" box (buried adj oxide) (silicon near epitax\$8)) same (sige gesi (silicon near germanium))	US-PGPUB; USPAT	OR	ON	2005/05/26 17:30
L15	300	L14 and ((source drain) with (elevat\$10 rais\$6))	US-PGPUB; USPAT	OR	ON	2005/05/26 17:30

L16	72	L15 and L9	US-PGPUB; USPAT	OR	ON	2005/05/26 17:30
L17	59	L15 and ((gate channel) near2 (recess\$6 trench groove damascene inlaid "in-laid"))	US-PGPUB; USPAT	OR	ON	2005/05/26 17:34
L18	335	(soi "silicon-on-insulator" "silicon-on-sapphire" box (buried adj oxide) (silicon near epitax\$8)) and (sige gesi (silicon near germanium))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 17:38
L19	8	L18 and ((gate channel) with (recess\$6 trench groove damascene inlaid "in-laid"))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 17:38
L20	2	L18 and ((source drain) same (elevat\$10 rais\$6))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 17:38
L21	979	9 and (sige gesi (silicon near germanium))	US-PGPUB; USPAT	OR	ON	2005/05/26 17:40